

DP2301S

DP2301S P-Channel MOSFET

General description

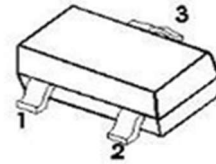
P-Channel MOSFET

Features:

- $V_{DS} : -20V$
- $I_D : -2.3A$
- $R_{DS(ON)}$ (at $V_{GS}=-4.5V$) < 140 mohm
- $R_{DS(ON)}$ (at $V_{GS}=-2.5V$) < 210 mohm
- Trench Power MOSFET technology
- Low $R_{DS(ON)}$ @ $V_{GS} = -4.5V$
- High Current Handling Capability
- Halogen-free 、RoHS Compliant

Applications

- DC/DC Converter for Portable Devices
- High-side Load Switch
- High Speed line Driver



1. Gate
2. Source
3. Drain

Package : SOT-23

Device Marking Code:

| Device Type | Device Marking |
|-------------|----------------|
| DP2301S | A1SHB |

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

| Parameters | Symbol | Value | Unit |
|--|-----------------|----------|---------------|
| Drain-Source Voltage | V_{DS} | -20 | V |
| Gate-Source Voltage | V_{GS} | ± 10 | V |
| Continuous Drain Current | I_D | -2.3 | A |
| Pulsed Drain Current (note 1) | I_{DM} | -9 | A |
| Maximum Power Dissipation | P_D | 1.0 | W |
| Thermal Resistance from Junction to Ambient (note 2) | $R_{\theta JA}$ | 125 | $^{\circ}C/W$ |
| Junction and Storage Temperature | T_J, T_{STG} | -50~+150 | $^{\circ}C$ |

DP2301S

Electrical Characteristics (T_j=25°C unless otherwise noted)

| Parameters | Symbol | Test Condition | Min | Typ | Max | Unit |
|---|----------------------|--|------|-------|------|------|
| Static Characteristics | | | | | | |
| Drain-source breakdown voltage | V _{(BR)DSS} | V _{GS} = 0V, I _D = - 250μA | -20 | -- | -- | V |
| Zero gate voltage drain current | I _{DSS} | V _{DS} = - 20V, V _{GS} = 0V | -- | -- | -1 | μA |
| Gate-body leakage current | I _{GSS} | V _{GS} = ± 10V, V _{DS} = 0V | -- | -- | ±100 | nA |
| Gate threshold voltage (note 3) | V _{GS(th)} | V _{DS} =V _{GS} , I _D = - 250μA | -0.4 | -0.6 | -1.0 | V |
| Drain-source on-resistance (note 3) | R _{DS(on)} | V _{GS} = - 4.5V, I _D = - 2A | -- | 125 | 140 | mΩ |
| | | V _{GS} = - 3.3V, I _D = - 1A | -- | 140 | 170 | mΩ |
| | | V _{GS} = - 2.5V, I _D = - 1A | -- | 170 | 210 | mΩ |
| Diode forward voltage (note 3) | V _{SD} | I _S = - 1A, V _{GS} = 0V | -- | -0.83 | -1.2 | V |
| Dynamic Characteristics (note 4) | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} = -10V, V _{GS} = 0V, f = 1MHz | -- | 177 | -- | pF |
| Output Capacitance | C _{oss} | | -- | 30 | -- | pF |
| Reverse Transfer Capacitance | C _{rss} | | -- | 25 | -- | pF |
| Switching Characteristics (note 4) | | | | | | |
| Turn-on delay time | t _{d(on)} | V _{DD} = -10V, I _D = -2A, R _G = 3.3Ω, V _{GS} = -4.5V | -- | 11 | -- | ns |
| Turn-on rise time | t _r | | -- | 32 | -- | ns |
| Turn-off delay time | t _{d(off)} | | -- | 25 | -- | ns |
| Turn-off fall time | t _f | | -- | 38 | -- | ns |
| Total Gate Charge | Q _g | V _{DS} = -10V, I _D = -2A, V _{GS} = -4.5V | -- | 5.3 | -- | nC |
| Gate-Source Charge | Q _{gs} | | -- | 0.7 | -- | nC |
| Gate-Drain Charge | Q _{gd} | | -- | 1.4 | -- | nC |

Note:

- 1.Repetitive rating: Pluse width limited by maximum junction temperature
- 2.Surface Mounted on FR4 board, t ≤ 10 sec.
- 3.Pulse test : Pulse width ≤ 300μs, duty cycle ≤ 2%. Guaranteed by design, not subject to production.

Typical Performance Characteristics

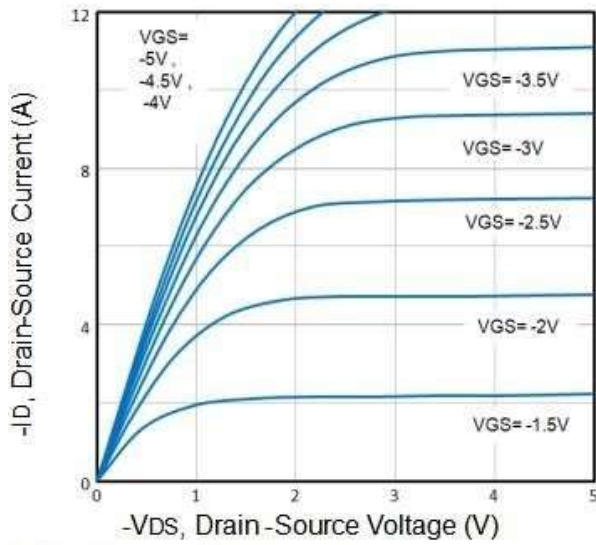


Fig1. Typical Output Characteristics

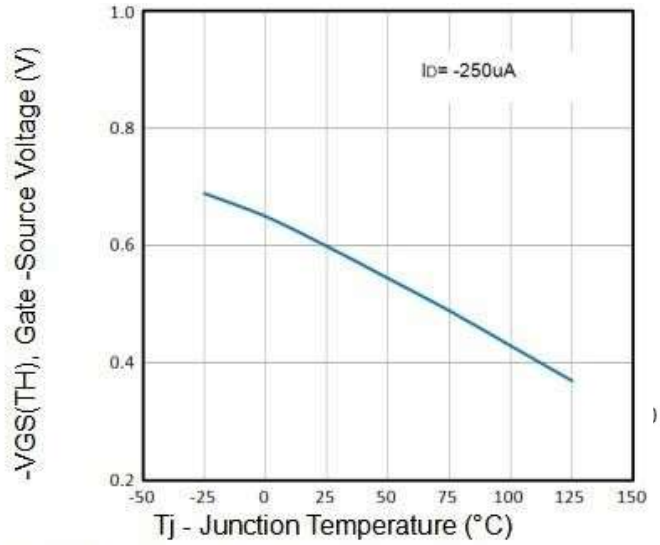


Fig2. Normalized Threshold Voltage Vs. Temperature

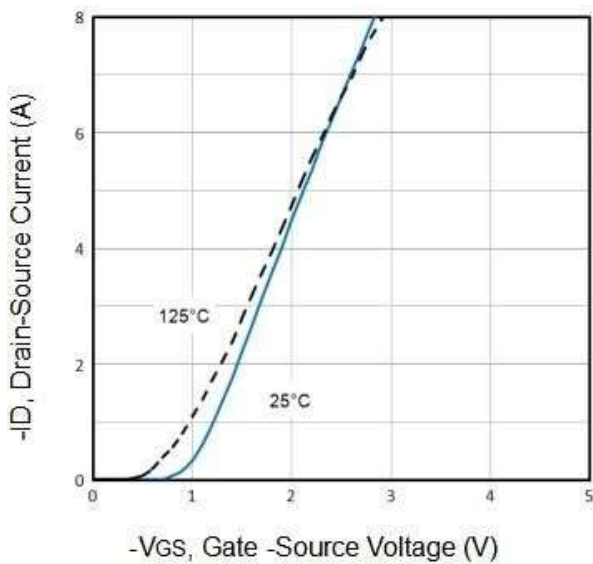


Fig3. Typical Transfer Characteristics

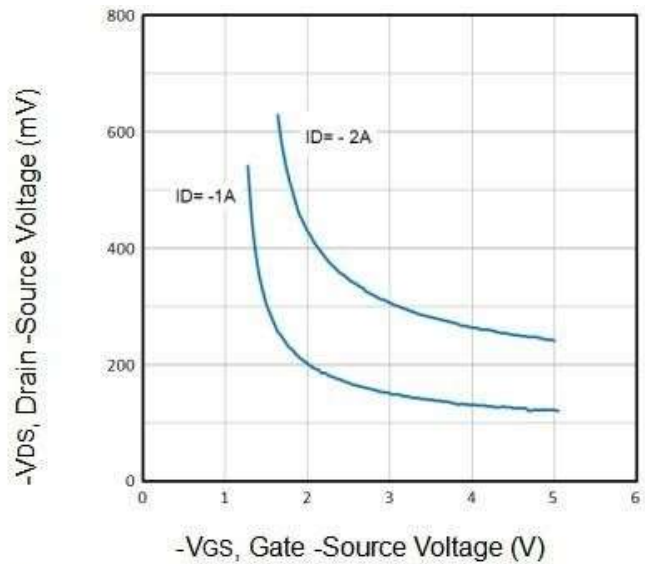


Fig4. Drain-Source Voltage vs Gate-Source Voltage

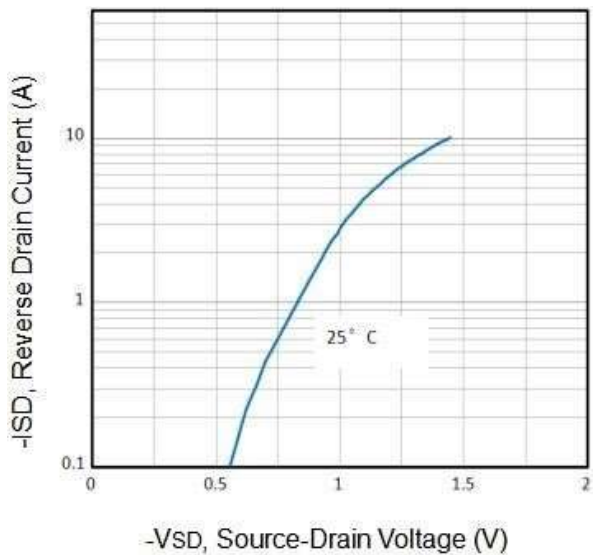


Fig5. Typical Source-Drain Diode Forward Voltage

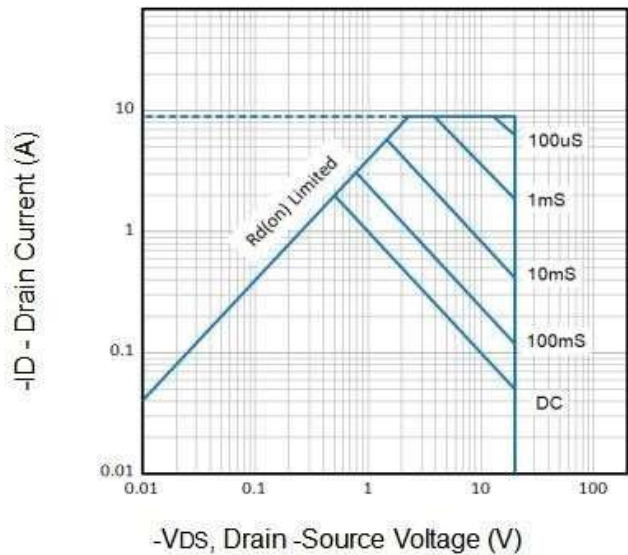


Fig6. Maximum Safe Operating Area

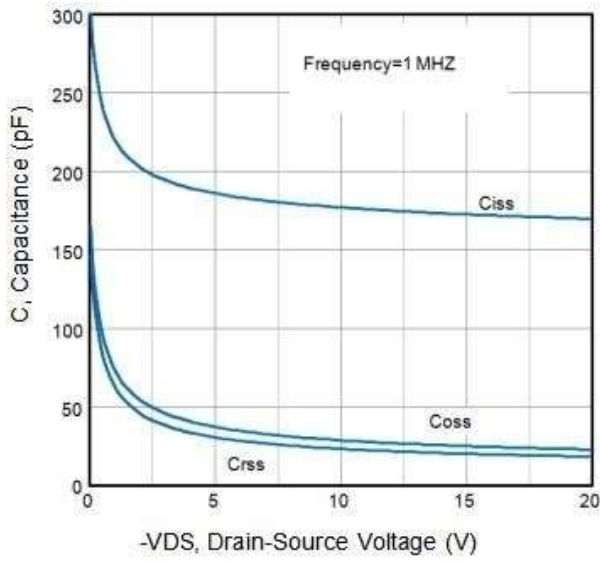


Fig7. Typical Capacitance Vs. Drain-Source Voltage

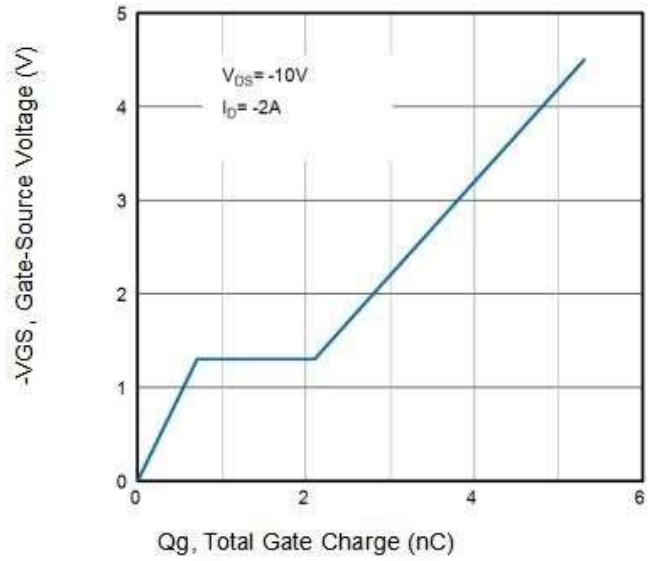
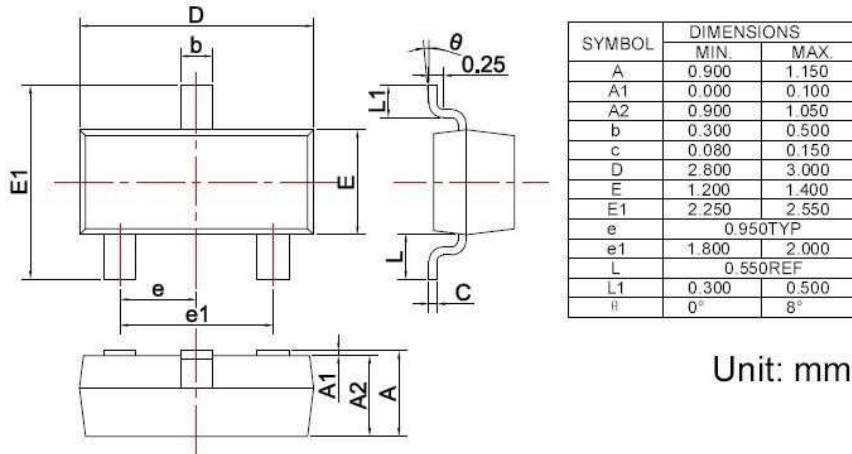
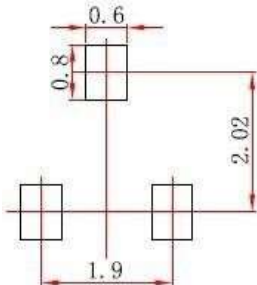


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

SOT-23 Package Outline Dimensions



Precautions: PCB Design



- Note:
1. Controlling dimension: In millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.

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